



ALPHA & OMEGA
SEMICONDUCTOR

AO4464

N-Channel Enhancement Mode Field Effect Transistor

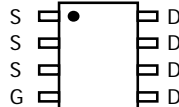


General Description

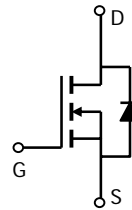
The AO4464 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. This device is suitable for use as a load switch or in PWM applications. The source leads are separated to allow a Kelvin connection to the source, which may be used to bypass the source inductance. *Standard Product AO4464 is Pb-free (meets ROHS & Sony 259 specifications). AO4464L is a Green Product ordering option. AO4464 and AO4464L are electrically identical.*

Features

V_{DS} (V) = 30V
 I_D = 8.5A (V_{GS} = 10V)
 $R_{DS(ON)} < 26m\Omega$ (V_{GS} = 10V)
 $R_{DS(ON)} < 40m\Omega$ (V_{GS} = 4.5V)



SOIC-8



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^A	I_D	8.5	A
$T_A=25^\circ\text{C}$			
$T_A=70^\circ\text{C}$		7.1	
Pulsed Drain Current ^B	I_{DM}	50	
Power Dissipation	P_D	3	W
$T_A=25^\circ\text{C}$			
$T_A=70^\circ\text{C}$		2.1	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	31	40	$^\circ\text{C/W}$
$t \leq 10\text{s}$				
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	59	75	$^\circ\text{C/W}$
Steady-State				
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	16	24	$^\circ\text{C/W}$
Steady-State				

Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=24\text{V}$, $V_{GS}=0\text{V}$ $T_J=55^{\circ}\text{C}$		0.004	1 5	μA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 20\text{V}$			100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	1	1.7	3	V
$I_{D(ON)}$	On state drain current	$V_{GS}=4.5\text{V}$, $V_{DS}=5\text{V}$	20			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}$, $I_D=8.5\text{A}$ $T_J=125^{\circ}\text{C}$		20 29.2	26 38	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}$, $I_D=5\text{A}$		31	40	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS}=5\text{V}$, $I_D=5\text{A}$	10	17		S
V_{SD}	Diode Forward Voltage	$I_S=1\text{A}$, $V_{GS}=0\text{V}$		0.76	1	V
I_S	Maximum Body-Diode Continuous Current				4.3	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=15\text{V}$, $f=1\text{MHz}$		680	820	pF
C_{oss}	Output Capacitance			102		pF
C_{rss}	Reverse Transfer Capacitance			77		pF
R_g	Gate resistance	$V_{GS}=0\text{V}$, $V_{DS}=0\text{V}$, $f=1\text{MHz}$		3	3.6	Ω
SWITCHING PARAMETERS						
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS}=10\text{V}$, $V_{DS}=15\text{V}$, $I_D=8.5\text{A}$		13.84	17	nC
$Q_g(4.5\text{V})$	Total Gate Charge			6.74	8.1	nC
Q_{gs}	Gate Source Charge			1.84		nC
Q_{gd}	Gate Drain Charge			3.32		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=10\text{V}$, $V_{DS}=15\text{V}$, $R_L=1.8\Omega$, $R_{GEN}=3\Omega$		4.5	6.5	ns
t_r	Turn-On Rise Time			4.2	6.3	ns
$t_{D(off)}$	Turn-Off DelayTime			20.1	30	ns
t_f	Turn-Off Fall Time			4.9	7.5	ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=8.5\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		17.2	21	ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=8.5\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		8.6	10	nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^{\circ}\text{C}$. The value in any given application depends on the user's specific board design. The current rating is based on the $t \leq 10\text{s}$ thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using 80 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^{\circ}\text{C}$. The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

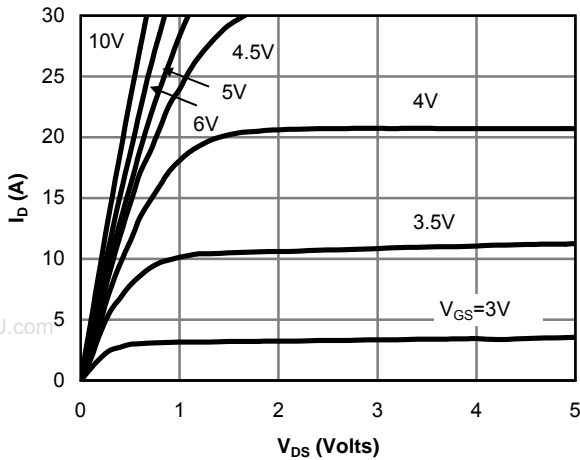


Fig 1: On-Region Characteristics

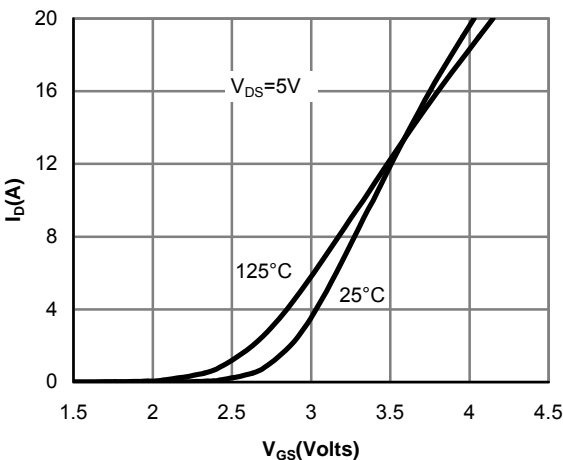


Figure 2: Transfer Characteristics

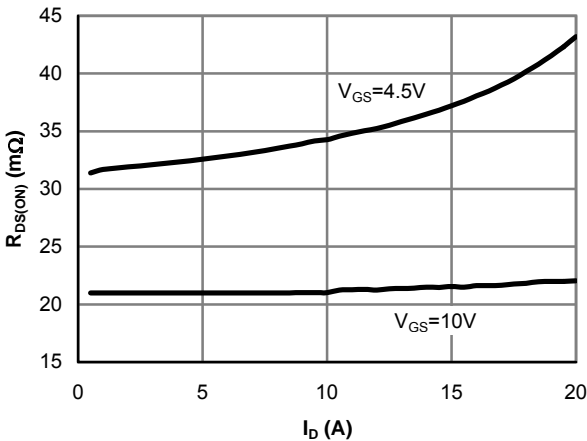


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

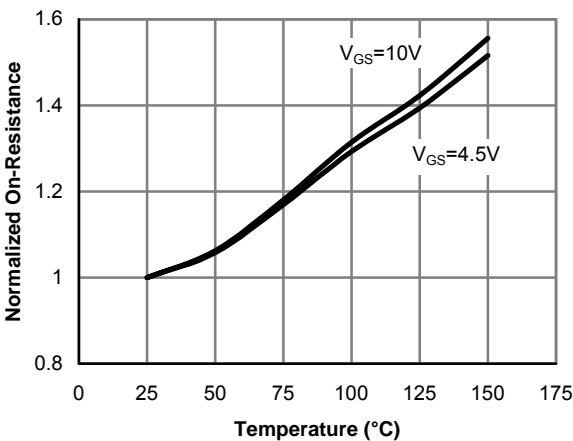


Figure 4: On-Resistance vs. Junction Temperature

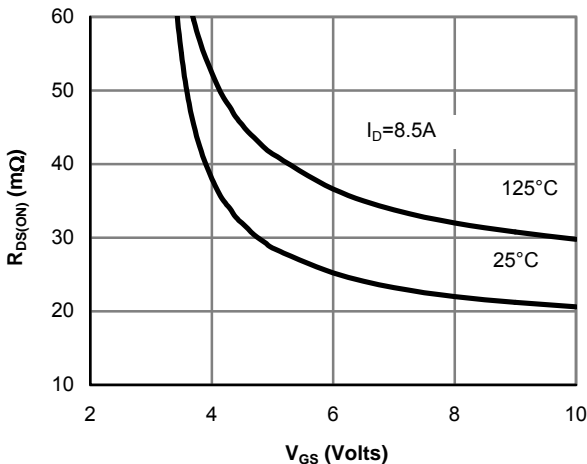


Figure 5: On-Resistance vs. Gate-Source Voltage

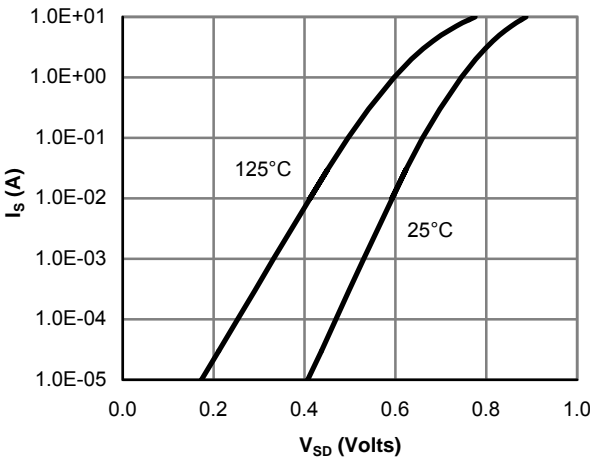


Figure 6: Body-Diode Characteristics

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